

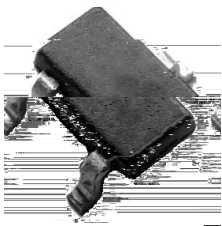


Rev. F Dec.-2019

SOT23-3 N CHANNEL MOSFET in a SOT23-3 Plastic Package.

$V_{DS}(V) = 30V$
 $I_D = 5.8\text{ A } (V_{GS} = 10V)$
 $R_{DS(ON)} < 32m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 36m\Omega (V_{GS} = 4V)$
 $R_{DS(ON)} < 56m\Omega (V_{GS} = 2V)$
无卤产品。HF Product.

This device is suitable for switch or in PWM applications.



PIN1 G PIN 2 D

Marking

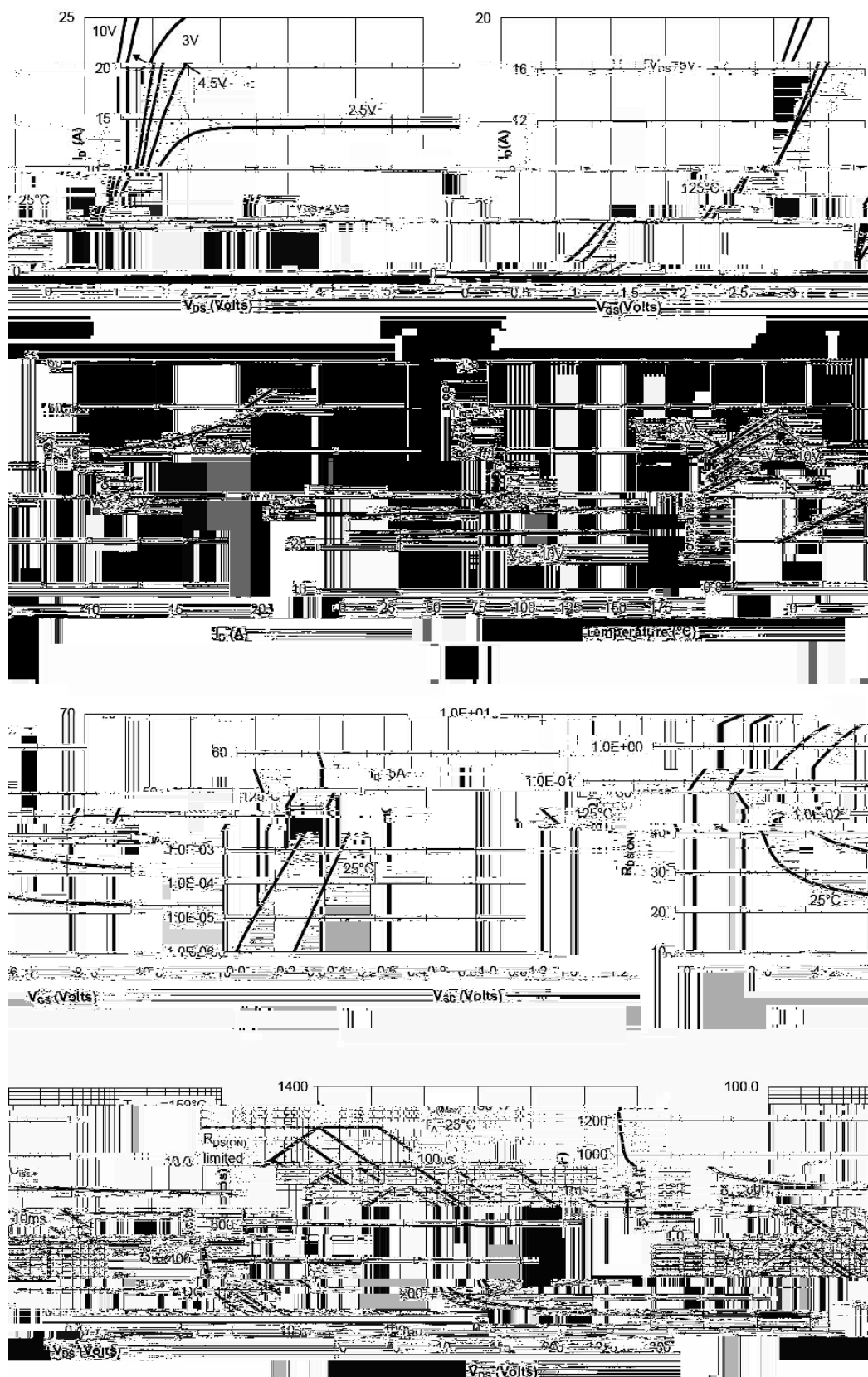
Rev. F Dec.-2019



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1MHz$		823	1030	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$, $f=1MHz$		1.2	3.6	Ω
Total Gate Charge	Q_g	$V_{GS}=4.5V$, $V_{DS}=15V$, $I_D=5.8A$		9.7	12	nC
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $R_L=2.7\Omega$ $V_{DS}=15V$ $R_{GEN}=3\Omega$		3.3	5	ns
Turn-On Rise Time	t_r			4.8	7	
Turn-Off Delay Time	$t_{d(off)}$			26.3	40	
Turn-Off Fall Time	t_f			4.1	6	
Body Diode Reverse Recovery Time	t_{rr}	$I_F=5A$ $dI/dt=100A/\mu s$		16	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=5A$ $dI/dt=100A/\mu s$		8.9	12	nC

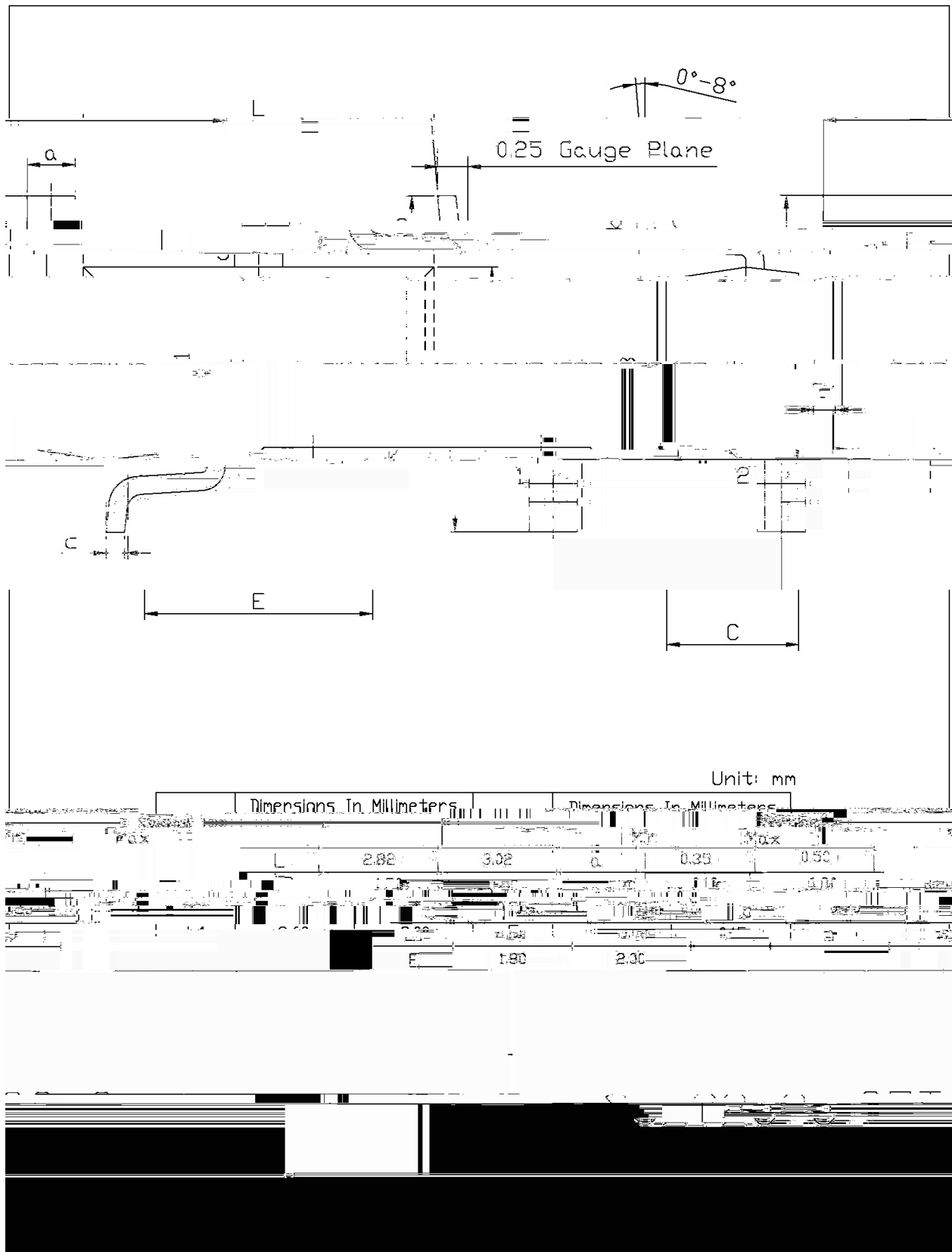


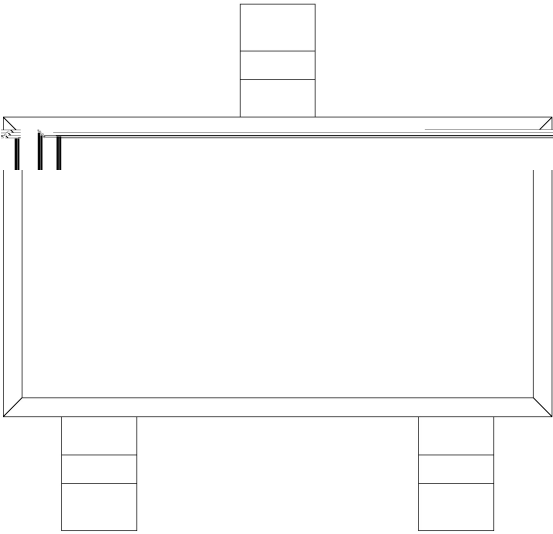
Rev. F Dec.-2019





Rev. F Dec.-2019



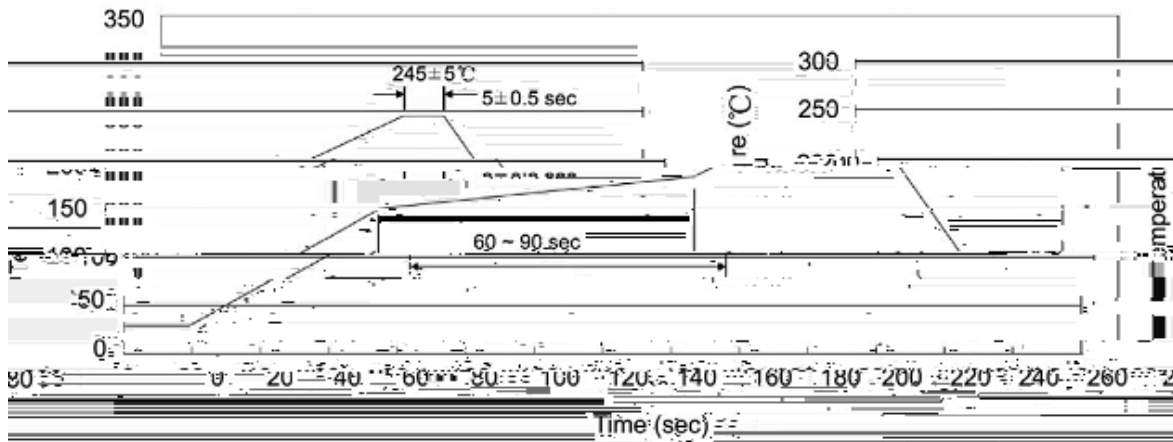


x



Rev. F Dec.-2019

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | |
|---|-----------|-------------|---|
| 1 | 150 ~ 180 | 60 ~ 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 ~ 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23-3	3,000	10	30,000	4	120,000	7" ×8	210×205×205	445×230×435